Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	HDMI-CEC, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	39
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 13x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f051c8t6

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32F051xx microcontrollers.

This document should be read in conjunction with the STM32F0xxxx reference manual (RM0091). The reference manual is available from the STMicroelectronics website *www.st.com*.

For information on the ARM® Cortex®-M0 core, please refer to the Cortex®-M0 Technical Reference Manual, available from the www.arm.com website.

2 Description

The STM32F051xx microcontrollers incorporate the high-performance ARM® Cortex®-M0 32-bit RISC core operating at up to 48 MHz frequency, high-speed embedded memories (up to 64 Kbytes of Flash memory and 8 Kbytes of SRAM), and an extensive range of enhanced peripherals and I/Os. All devices offer standard communication interfaces (up to two I^2Cs, up to two SPIs, one I^2S, one HDMI CEC and up to two USARTs), one 12-bit ADC, one 12-bit DAC, six 16-bit timers, one 32-bit timer and an advanced-control PWM timer.

The STM32F051xx microcontrollers operate in the -40 to +85 °C and -40 to +105 °C temperature ranges, from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving modes allows the design of low-power applications.

The STM32F051xx microcontrollers include devices in seven different packages ranging from 32 pins to 64 pins with a die form also available upon request. Depending on the device chosen, different sets of peripherals are included.

These features make the STM32F051xx microcontrollers suitable for a wide range of applications such as application control and user interfaces, hand-held equipment, A/V receivers and digital TV, PC peripherals, gaming and GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms and HVACs.

In Standby mode, it is put in power down mode. In this mode, the regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption (but the contents of the registers and SRAM are lost).

3.5.4 Low-power modes

The STM32F051xx microcontrollers support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  Stop mode achieves very low power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low power mode.

  The device can be woken up from Stop mode by any of the EXTI lines. The EXTI line source can be one of the 16 external lines, the PVD output, RTC, I2C1, USART1,, COMPx or the CEC.

  The CEC, USART1 and I2C1 peripherals can be configured to enable the HSI RC oscillator so as to get clock for processing incoming data. If this is used when the voltage regulator is put in low power mode, the regulator is first switched to normal mode before the clock is provided to the given peripheral.

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the RTC domain and Standby circuitry.

  The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pins, or an RTC event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.

3.6 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-32 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the application to configure the frequency of the AHB and the APB domains. The maximum frequency of the AHB and the APB domains is 48 MHz.

hardware touch sensing controller and only requires few external components to operate. For operation, one capacitive sensing GPIO in each group is connected to an external capacitor and cannot be used as effective touch sensing channel.

The touch sensing controller is fully supported by the STMTouch touch sensing firmware library, which is free to use and allows touch sensing functionality to be implemented reliably in the end application.

Table 5. Capacitive sensing GPIOs available on STM32F051xx devices

Group	Capacitive sensing signal name	Pin name	Group	Capacitive sensing signal name	Pin name
1	TSC_G1_IO1	PA0	4	TSC_G4_IO1	PA9
	TSC_G1_IO2	PA1		TSC_G4_IO2	PA10
	TSC_G1_IO3	PA2		TSC_G4_IO3	PA11
	TSC_G1_IO4	PA3		TSC_G4_IO4	PA12
2	TSC_G2_IO1	PA4	5	TSC_G5_IO1	PB3
	TSC_G2_IO2	PA5		TSC_G5_IO2	PB4
	TSC_G2_IO3	PA6		TSC_G5_IO3	PB6
	TSC_G2_IO4	PA7		TSC_G5_IO4	PB7
3	TSC_G3_IO1	PC5	6	TSC_G6_IO1	PB11
	TSC_G3_IO2	PB0		TSC_G6_IO2	PB12
	TSC_G3_IO3	PB1		TSC_G6_IO3	PB13
	TSC_G3_IO4	PB2		TSC_G6_IO4	PB14

Table 6. Effective number of capacitive sensing channels on STM32F051xx

Analog I/O group	Number of capacitive sensing channels				
	STM32F051Rx	STM32F051Cx	STM32F051Tx	STM32F051KxU (UFQFPN32)	STM32F051KxT (LQFP32)
G1	3	3	3	3	3
G2	3	3	3	3	3
G3	3	2	2	2	1
G4	3	3	3	3	3
G5	3	3	3	3	3
G6	3	3	0	0	0
Number of capacitive sensing channels	18	17	14	14	13

3.18 Serial peripheral interface (SPI) / Inter-integrated sound interface (I^2S)

Up to two SPIs are able to communicate up to 18 Mbit/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame size is configurable from 4 bits to 16 bits.

One standard I^2S interface (multiplexed with SPI1) supporting four different audio standards can operate as master or slave at half-duplex communication mode. It can be configured to transfer 16 and 24 or 32 bits with 16-bit or 32-bit data resolution and synchronized by a specific signal. Audio sampling frequency from 8 kHz up to 192 kHz can be set by an 8-bit programmable linear prescaler. When operating in master mode, it can output a clock for an external audio component at 256 times the sampling frequency.

Table 11. STM32F051xx SPI/I^2S implementation

SPI features(1)	SPI1	SPI2
Hardware CRC calculation	X	X
Rx/Tx FIFO	X	X
NSS pulse mode	X	X
I^2S mode	X	-
TI mode	X	X

1. X = supported.

3.19 High-definition multimedia interface (HDMI) - consumer electronics control (CEC)

The device embeds a HDMI-CEC controller that provides hardware support for the Consumer Electronics Control (CEC) protocol (Supplement 1 to the HDMI standard).

This protocol provides high-level control functions between all audiovisual products in an environment. It is specified to operate at low speeds with minimum processing and memory overhead. It has a clock domain independent from the CPU clock, allowing the HDMI_CEC controller to wakeup the MCU from Stop mode on data reception.

3.20 Serial wire debug port (SW-DP)

An ARM SW-DP interface is provided to allow a serial wire debugging tool to be connected to the MCU.

Table 13. Pin definitions (continued)

Pin number						Pin name (function upon reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP64	UFBGA64	LQFP48/UFQFPN48	WLCSP36	LQFP32	UFQFPN32					Alternate functions	Additional functions
58	D3	42	C4	29	29	PB6	I/O	FTf	-	I2C1_SCL, USART1_TX, TIM16_CH1N, TSC_G5_IO3	-
59	C3	43	A4	30	30	PB7	I/O	FTf	-	I2C1_SDA, USART1_RX, TIM17_CH1N, TSC_G5_IO4	-
60	B4	44	B4	31	31	BOOT0	I	B	-	Boot memory selection	
61	B3	45	-	-	32	PB8	I/O	FTf	(4)(5)	I2C1_SCL, CEC, TIM16_CH1, TSC_SYNC	-
62	A3	46	-	-	-	PB9	I/O	FTf	(5)	I2C1_SDA, IR_OUT, TIM17_CH1, EVENTOUT	-
63	D5	47	D6	32	0	VSS	S	-	-	Ground	
64	E5	48	A5	1	1	VDD	S	-	-	Digital power supply	

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
   - The speed should not exceed 2 MHz with a maximum load of 30 pF.
   - These GPIOs must not be used as current sources (e.g. to drive an LED).
2. After the first RTC domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the main reset. For details on how to manage these GPIOs, refer to the RTC domain and RTC register descriptions in the reference manual.
3. Distinct VSSA pin is only available on packages with 48 and more pins. For all other packages, the pin number corresponds to the VSS pin to which VSSA pad of the silicon die is connected.
4. On the LQFP32 package, PB2 and PB8 must be set to defined levels by software, as their corresponding pads on the silicon die are left unconnected. Apply the same recommendations as for unconnected pins.
5. On the WLCSP36 package, PB8, PB9, PB10, PB11, PB12, PB13, PB14 and PB15 must be set to defined levels by software, as their corresponding pads on the silicon die are left unconnected. Apply the same recommendations as for unconnected pins.
6. After reset, these pins are configured as SWDIO and SWCLK alternate functions, and the internal pull-up on the SWDIO pin and the internal pull-down on the SWCLK pin are activated.

5 Memory mapping

To the difference of STM32F051x8 memory map in *Figure 10*, the two bottom code memory spaces of STM32F051x4/STM32F051x6 end at 0x0000 3FFF/0x0000 7FFF and 0x0800 3FFF/0x0000 7FFF, respectively.

Figure 10. STM32F051x8 memory map

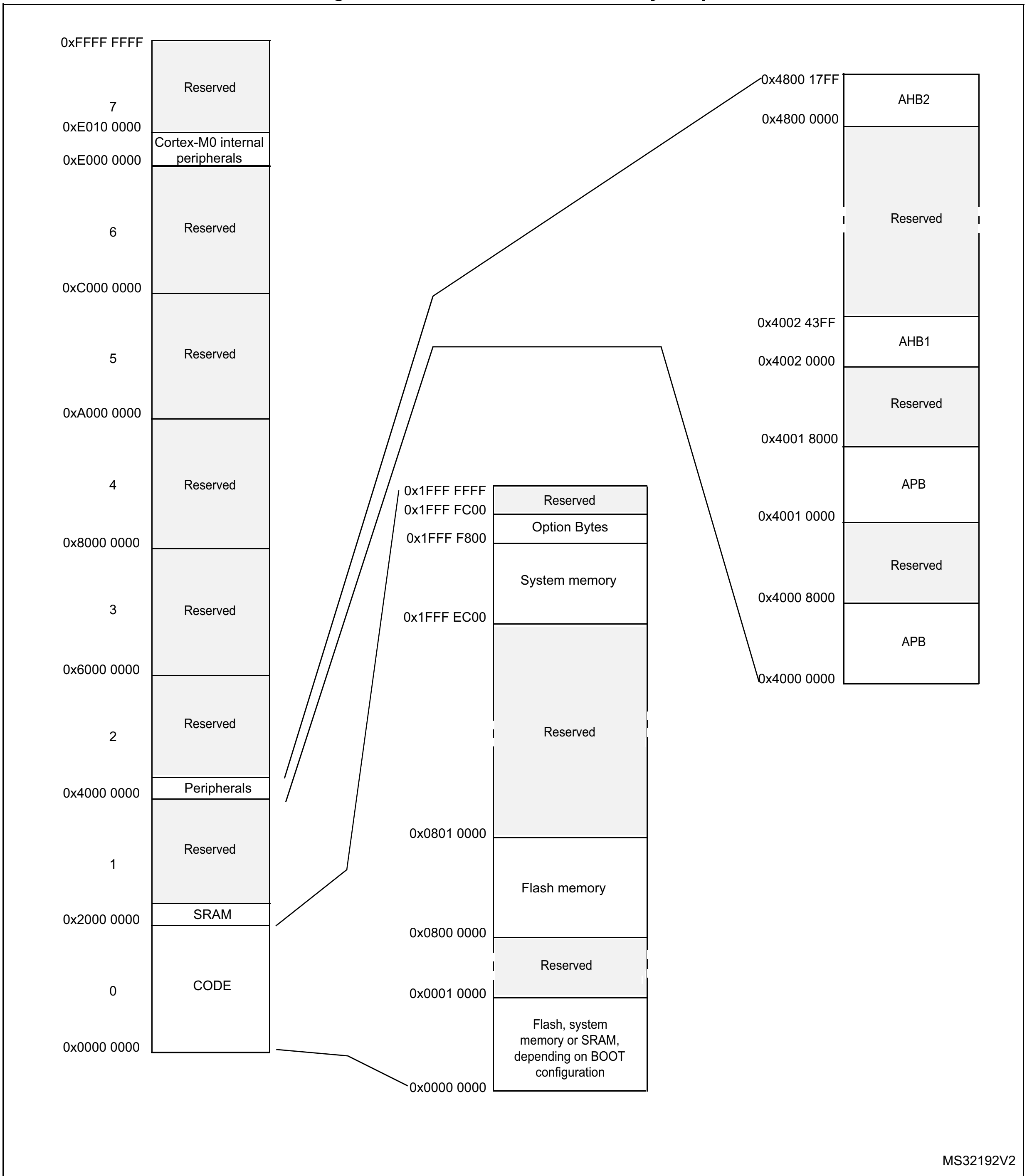


Table 18. Current characteristics

Symbol	Ratings	Max.	Unit
ΣI_{VDD}	Total current into sum of all VDD power lines (source)(1)	120	mA
ΣI_{VSS}	Total current out of sum of all VSS ground lines (sink)(1)	-120	
$I_{VDD(PIN)}$	Maximum current into each VDD power pin (source)(1)	100	
$I_{VSS(PIN)}$	Maximum current out of each VSS ground pin (sink)(1)	-100	
$I_{IO(PIN)}$	Output current sunk by any I/O and control pin	25	
	Output current source by any I/O and control pin	-25	
$\Sigma I_{IO(PIN)}$	Total output current sunk by sum of all I/Os and control pins(2)	80	
	Total output current sourced by sum of all I/Os and control pins(2)	-80	
$I_{INJ(PIN)}$(3)	Injected current on B, FT and FTf pins	-5/+0(4)	
	Injected current on TC and RST pin	± 5	
	Injected current on TTa pins(5)	± 5	
$\Sigma I_{INJ(PIN)}$	Total injected current (sum of all I/O and control pins)(6)	± 25	

1. All main power (VDD, VDDA) and ground (VSS, VSSA) pins must always be connected to the external power supply, in the permitted range.
2. This current consumption must be correctly distributed over all I/Os and control pins. The total output current must not be sunk/sourced between two consecutive power supply pins referring to high pin count QFP packages.
3. A positive injection is induced by $V_{IN} > V_{DDIOx}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 17: Voltage characteristics* for the maximum allowed input voltage values.
4. Positive injection is not possible on these I/Os and does not occur for input voltages lower than the specified maximum value.
5. On these I/Os, a positive injection is induced by $V_{IN} > V_{DDA}$. Negative injection disturbs the analog performance of the device. See note (2) below *Table 54: ADC accuracy*.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 19. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

Table 30. Switching output I/O current consumption

Symbol	Parameter	Conditions[(1)]	I/O toggling frequency (f_{SW})	Typ	Unit
I_{SW}	I/O current consumption	V_{DDIOx} = 3.3 V C = C_{INT}	4 MHz	0.07	mA
			8 MHz	0.15	
			16 MHz	0.31	
			24 MHz	0.53	
			48 MHz	0.92	
		V_{DDIOx} = 3.3 V C_{EXT} = 0 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.18	
			8 MHz	0.37	
			16 MHz	0.76	
			24 MHz	1.39	
			48 MHz	2.188	
		V_{DDIOx} = 3.3 V C_{EXT} = 10 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.32	
			8 MHz	0.64	
			16 MHz	1.25	
			24 MHz	2.23	
			48 MHz	4.442	
		V_{DDIOx} = 3.3 V C_{EXT} = 22 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.49	
			8 MHz	0.94	
			16 MHz	2.38	
			24 MHz	3.99	
		V_{DDIOx} = 3.3 V C_{EXT} = 33 pF C = C_{INT} + C_{EXT}+ C_S	4 MHz	0.64	
			8 MHz	1.25	
			16 MHz	3.24	
			24 MHz	5.02	
		V_{DDIOx} = 3.3 V C_{EXT} = 47 pF C = C_{INT} + C_{EXT}+ C_S C = C_{int}	4 MHz	0.81	
			8 MHz	1.7	
			16 MHz	3.67	
		V_{DDIOx} = 2.4 V C_{EXT} = 47 pF C = C_{INT} + C_{EXT}+ C_S C = C_{int}	4 MHz	0.66	
			8 MHz	1.43	
			16 MHz	2.45	
			24 MHz	4.97	

1. C_S = 7 pF (estimated value).

High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 35*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 35. HSE oscillator characteristics

Symbol	Parameter	Conditions(1)	Min(2)	Typ	Max(2)	Unit
f_{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R_F	Feedback resistor	-	-	200	-	kΩ
I_{DD}	HSE current consumption	During startup(3)	-	-	8.5	mA
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@8 MHz	-	0.4	-	
		V_{DD} = 3.3 V, Rm = 45 Ω, CL = 10 pF@8 MHz	-	0.5	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 5 pF@32 MHz	-	0.8	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@32 MHz	-	1	-	
		V_{DD} = 3.3 V, Rm = 30 Ω, CL = 20 pF@32 MHz	-	1.5	-	
g_m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{SU(HSE)}$(4)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Guaranteed by design, not tested in production.
3. This consumption level occurs during the first 2/3 of the $t_{SU(HSE)}$ startup time
4. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Table 42. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Min(1)	Unit
N_{END}	Endurance	T_A = –40 to +105 °C	10	kcycle
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Year
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycle(2) at T_A = 55 °C	20	

1. Data based on characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 43*. They are based on the EMS levels and classes defined in application note AN1709.

Table 43. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP64, T_A = +25 °C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP64, T_A = +25°C, f_{HCLK} = 48 MHz, conforming to IEC 61000-4-4	4B

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

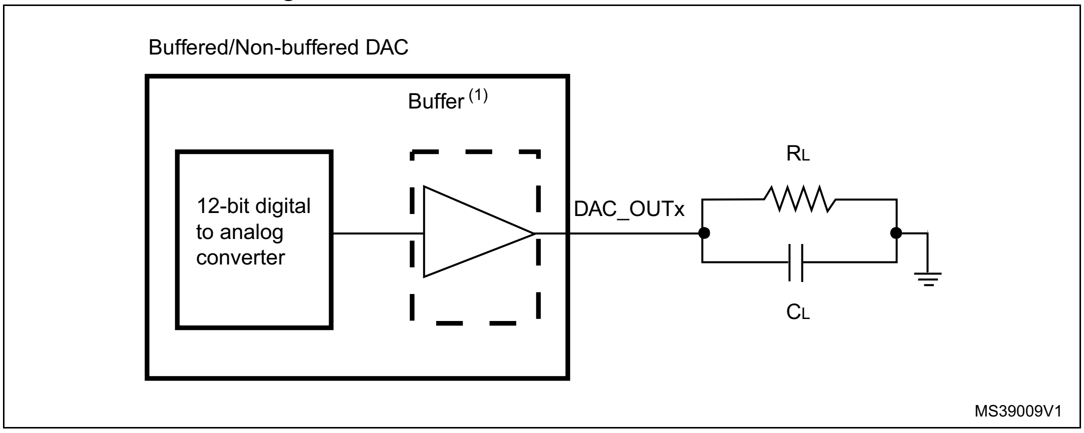
Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Table 55. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
Gain error(3)	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}$(3)	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	-	3	4	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
Update rate(3)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
t_{WAKEUP}(3)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ (1)	Power supply rejection ratio (to V_{DDA}) (static DC measurement	-	–67	–40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

1. Guaranteed by design, not tested in production.
2. The DAC is in “quiescent mode” when it keeps the value steady on the output so no dynamic consumption is involved.
3. Data based on characterization results, not tested in production.

Figure 27. 12-bit buffered / non-buffered DAC



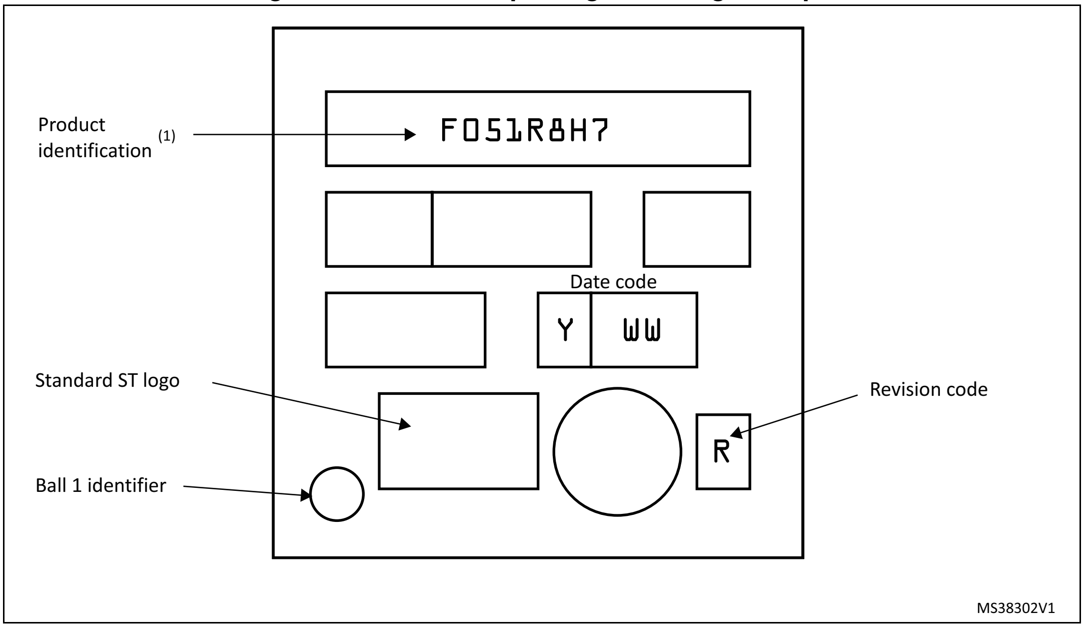
1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 36. UFBGA64 package marking example

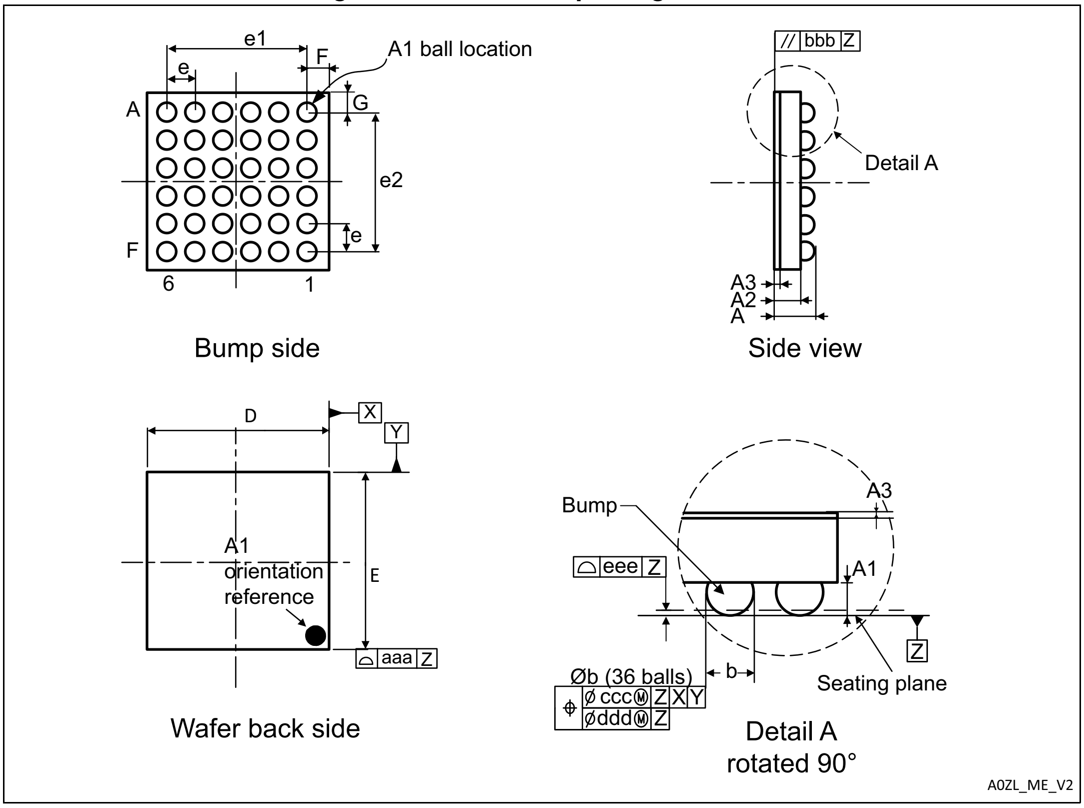


1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

7.5 WLCSP36 package information

WLCSP36 is a 36-ball, 2.605 x 2.703 mm, 0.4 mm pitch wafer-level chip-scale package.

Figure 46. WLCSP36 package outline



1. Drawing is not to scale.

Table 70. WLCSP36 package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3(2)	-	0.025	-	-	0.0010	-
b(3)	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	2.570	2.605	2.640	0.1012	0.1026	0.1039
E	2.668	2.703	2.738	0.1050	0.1064	0.1078
e	-	0.400	-	-	0.0157	-
e1	-	2.000	-	-	0.0787	-
e2	-	2.000	-	-	0.0787	-

Table 70. WLCSP36 package mechanical data (continued)

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
F	-	0.3025	-	-	0.0119	-
G	-	0.3515	-	-	0.0138	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 47. Recommended pad footprint for WLCSP36 package

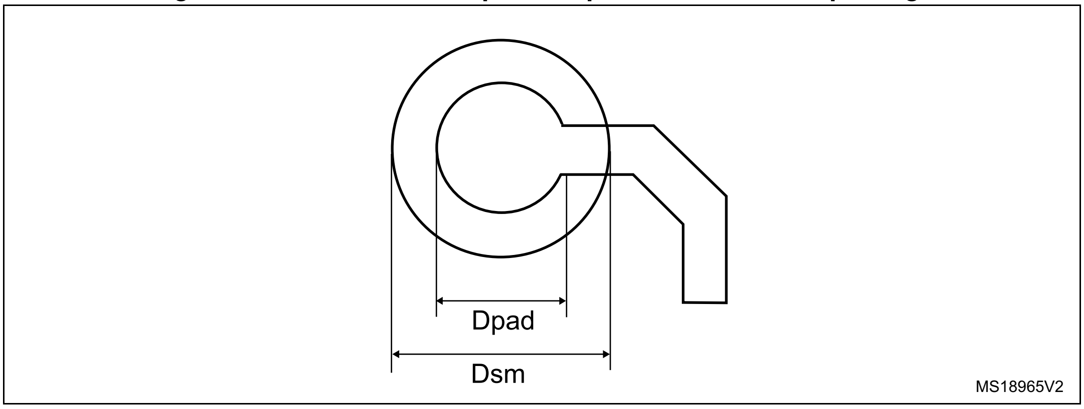


Table 71. WLCSP36 recommended PCB design rules

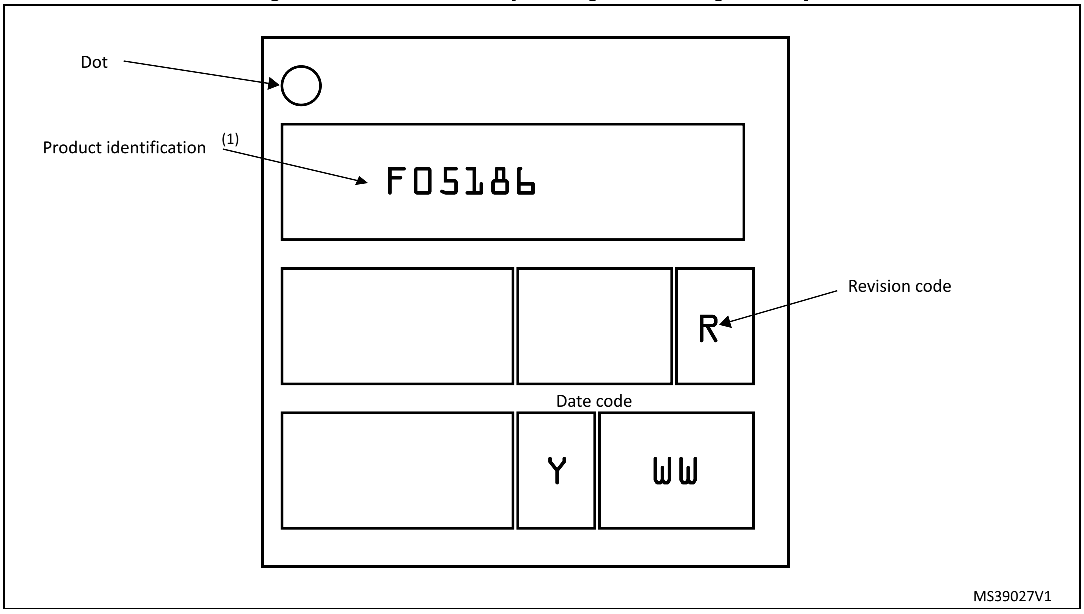
Dimension	Recommended values
Pitch	0.4 mm
Dpad	260 µm max. (circular) 220 µm recommended
Dsm	300 µm min. (for 260 µm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 48. WLCSP36 package marking example



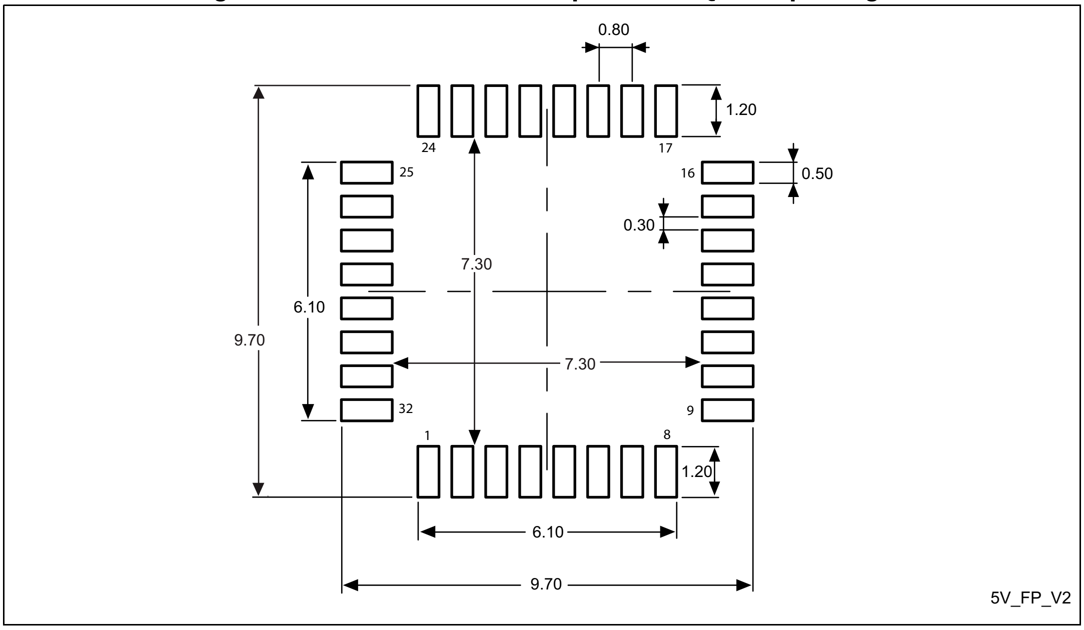
1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 72. LQFP32 package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.300	0.370	0.450	0.0118	0.0146	0.0177
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.600	-	-	0.2205	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.600	-	-	0.2205	-
e	-	0.800	-	-	0.0315	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.100	-	-	0.0039

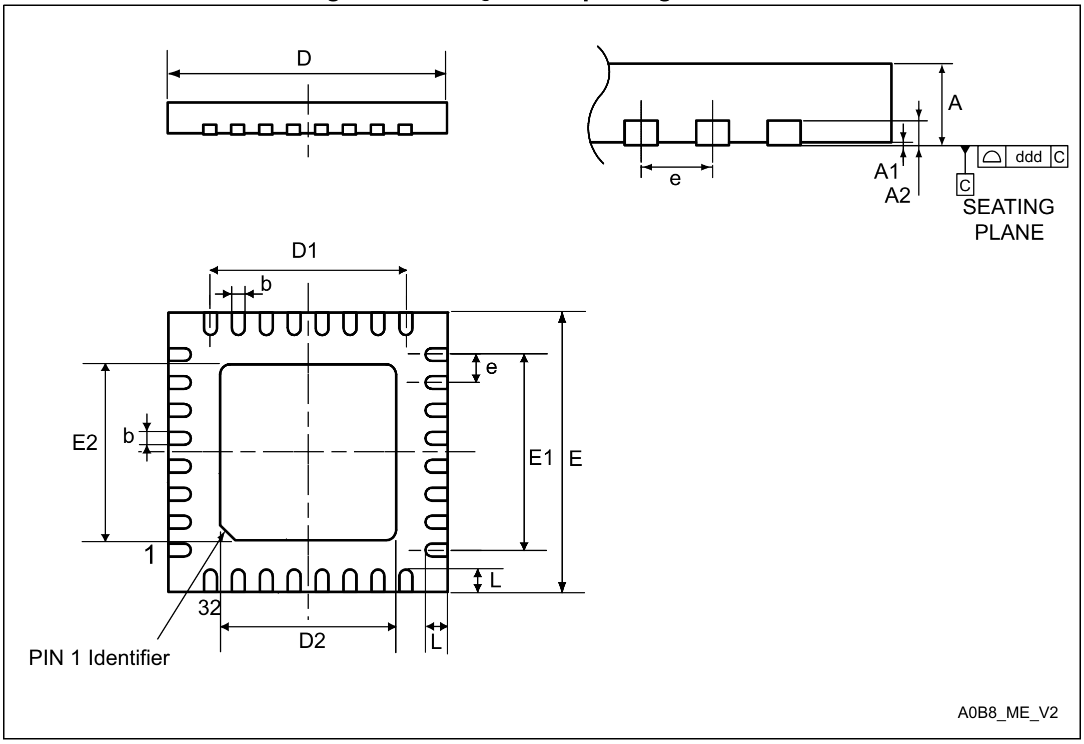
1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 50. Recommended footprint for LQFP32 package



1. Dimensions are expressed in millimeters.

Figure 52. UFQFPN32 package outline



1. Drawing is not to scale.
2. All leads/pads should also be soldered to the PCB to improve the lead/pad solder joint life.
3. There is an exposed die pad on the underside of the UFQFPN package. This pad is used for the device ground and must be connected. It is referred to as pin 0 in *Table: Pin definitions*.

7.8 Thermal characteristics

The maximum chip junction temperature ($T_J$max) must never exceed the values given in *Table 20: General operating conditions*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

$$T_J \text{ max} = T_A \text{ max} + (P_D \text{ max} \times \Theta_{JA})$$

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma ((V_{DDIOx} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 74. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP64 - 10 × 10 mm / 0.5 mm pitch	45	°C/W
	Thermal resistance junction-ambient LQFP48 - 7 × 7 mm	55	
	Thermal resistance junction-ambient LQFP32 - 7 × 7 mm	56	
	Thermal resistance junction-ambient UFBGA64 - 5 × 5 mm	65	
	Thermal resistance junction-ambient UFQFPN48 - 7 × 7 mm	32	
	Thermal resistance junction-ambient UFQFPN32 - 5 × 5 mm	38	
	Thermal resistance junction-ambient WLCSP36 - 2.6 × 2.7 mm	60	

7.8.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

7.8.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in *Section 8: Ordering information*.

Table 76. Document revision history (continued)

Date	Revision	Changes
13-Jan-2014	4	Modified datasheet title. Added packages UFQFPN48 and UFBGA64. Replaced "backup domain with "RTC domain" throughout the document. Changed SRAM value from "4 to 8 Kbyte" to "8 Kbyte" Replaced IWWDG with IWDG in *Figure: Block diagram.* Added inputs LSI and LSE to the multiplexer in *Figure: Clock tree.* Added feature "Reference clock detection" in *Section: Real-time clock (RTC) and backup registers.* Modified junction temperature in *Table: Thermal characteristics.* Renamed *Table: Internal voltage reference calibration values*. Replaced V_{DD} with V_{DDA} and V_{RERINT} with ΔV_{REFINT} in *Table: Embedded internal reference voltage.* Rephrased introduction of *Section: Touch sensing controller (TSC).* Rephrased *Section: Voltage regulator.* Added sentence "If this is used when the voltage regulator is put in low power mode..." under "Stop mode" in *Section: Low-power modes.* Removed sentence "The internal voltage reference is also connected to ADC_IN17 input channel of the ADC." in *Section: Comparators (COMP).* Removed feature "Periodic wakeup from Stop/Standby" in *Section: Real-time clock (RTC) and backup registers.* Replaced I_{DD} with I_{DDA} in *Table: HSI oscillator characteristics, Table: HSI14 oscillator characteristics* and *Table: LSI oscillator characteristics*. Moved section "Wakeup time from low-power mode" to *Section 6.3.6* and rephrased the section. Added lines D2 and E2 in *Table: UFQFPN48 – 7 x 7 mm, 0.5 mm pitch, package mechanical data.* Added "The peripheral clock used is 48 MHz." in Section *On-chip peripheral current consumption.*